

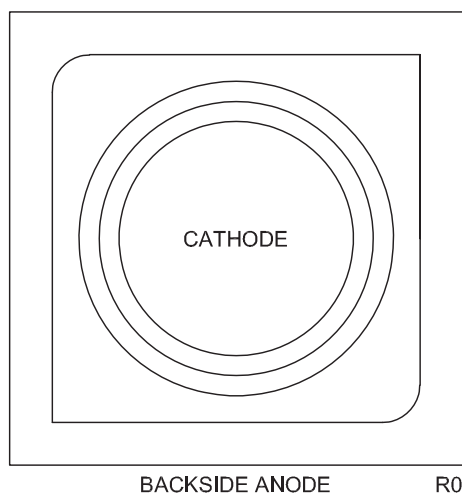
PROCESS CPZ35R
Transient Voltage Suppressor
3.3 Volt TVS Chip



PROCESS DETAILS

Die Size	10.2 x 10.2 MILS
Die Thickness	3.9 MILS
Cathode Bonding Pad Area	7.1 MILS DIAMETER
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



GROSS DIE PER 5 INCH WAFER

163,034

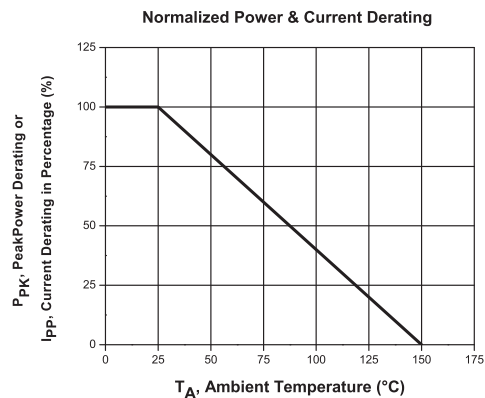
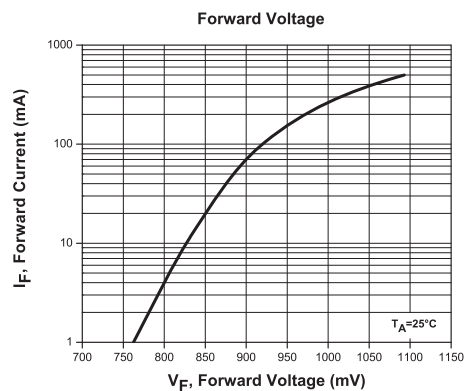
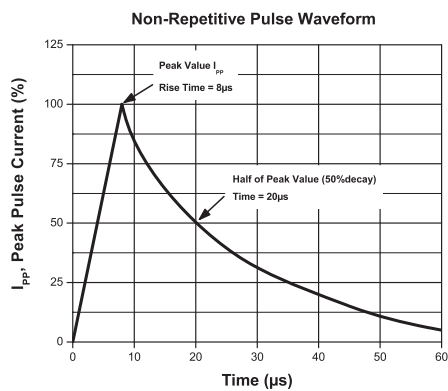
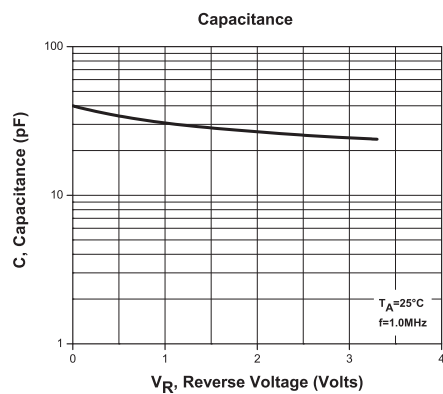
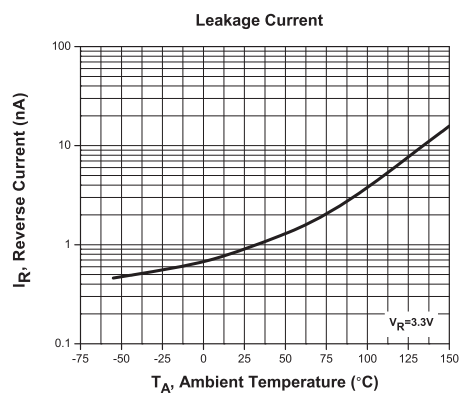
PRINCIPAL DEVICE TYPE

CMATVS3V3

R0 (5-January 2012)

PROCESS CPZ35R

Typical Electrical Characteristics



R0 (5-January 2012)